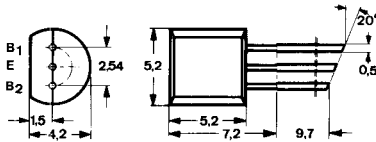


Silizium-Unijunction-Transistor Silicon Unijunction Transistor

Anwendungen: Ansteuerung von Thyristoren

Applications: Thyristor control

Abmessungen in mm
Dimensions in mm



Normgehäuse
Case
10 B 3 DIN 41 868
JEDEC TO 92
Gewicht · Weight
max. 0,4 g

Absolute Grenzdaten Absolute maximum ratings

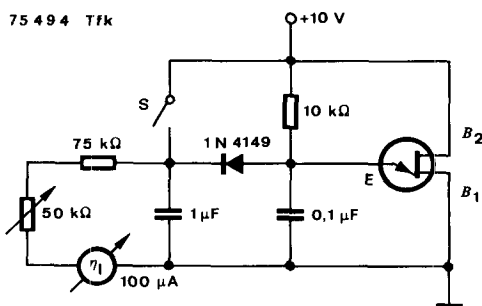
Interbasisspannung <i>Interbase voltage</i>	$U_{B1B2}^{1)}$	35	V
Emitter-Basis-1-Sperrspannung <i>Emitter-base-one voltage</i>	$-U_{EB1}$	35	V
Emitterstoßstrom <i>Emitter-surge current</i>	I_{ESM}	1,5	A
Gesamtverlustleistung <i>Total power dissipation</i> $t_{amb} \leq 25^{\circ}\text{C}$	P_{tot}	300	mW
Sperrschichttemperatur <i>Junction temperature</i>	t_j	125	$^{\circ}\text{C}$
Lagerungstemperaturbereich <i>Storage temperature range</i>	t_{stg}	-55 ... +125	$^{\circ}\text{C}$

¹⁾ $U_{B2B1} = \sqrt{r_{BB} \cdot P_{tot}}$

BSV 57 B

Kenngrößen Characteristics

	Min.	Typ.	Max.
$t_{amb} = 25^{\circ}\text{C}$			
Emittersperrstrom Emitter cut-off current $-U_{EB1} = 30\text{ V}$	$-I_{EB10}^{*)}$		20 nA
Emitter-Sättigungsspannung Emitter saturation voltage $U_{B2B1} = 10\text{ V}, I_E = 50\text{ mA}$	U_{EB1sat}	2	3 V
Höckerstrom Peak point current $U_{B2B1} = 25$	I_P		6 μA
Talstrom Valley point current $U_{B2B1} = 20\text{ V}, R_{B2} = 100\ \Omega$	I_V	4	mA
Interbasiswiderstand Interbase resistance $U_{B2B1} = 3\text{ V}, I_E = 0$	$r_{BB}^{*)}$	4,7	9,1 k Ω
Inneres Spannungsverhältnis Intrinsic stand-off ratio $U_{B2B1} = 10\text{ V}$	$\eta_i^{*)})$	0,68	0,82



Eichen: S-gedrückt
Calibration with
S-pressed

Meßschaltung für:
Test circuit for: η_i

*) AQL = 0,65%, $^1) \frac{t_p}{T} = 0,01, t_p = 0,3\text{ ms}$